

Features

- Uses CRM(CQ) advanced Trench MOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

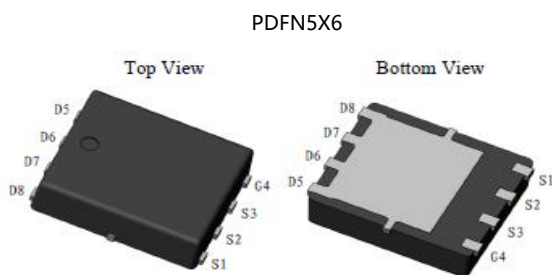
Product Summary

V_{DS}	30V
$R_{DS(on).typ}$	1.7mΩ
I_D	130A

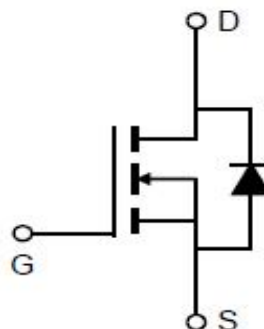
Applications

- Motor control and drive
- Battery management System
- UPS (Uninterruptible Power Supplies)

100% DVDS Tested
100% Avalanche Tested



CRTM024N03L4



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTM024N03L4	TM024N03L	PDFN5X6	Tape&Reel	N/A	N/A	5000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	30	V
Continuous drain current	I_D	130	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		83	A
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	520	A
Avalanche energy, single pulse ($I_D = 38\text{A}$, $R_g = 25\Omega$) ^[1]	E_{AS}	370	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	58	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$

※. Notes:

1.EAS is tested at starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $I_{AS} = 38\text{A}$, $V_{ds} = 30\text{V}$.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	2.17	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	64	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	30	-	-	V	$V_{GS}=0V, I_D=250\mu A$
		30	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{GS(th)}$	0.9	1.3	2.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=30V, V_{GS}=0V$ $T_j=25^\circ C$
		-	-	100		$T_j=125^\circ C$
Gate-source leakage current	I_{GSS}	-	-	±100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.7	2.2	mΩ	$V_{GS}=10V, I_D=19A$
		-	2.3	3.0		$V_{GS}=4.5V, I_D=19A$
Transconductance	g_{fs}	-	91	-	S	$V_{DS}=5V, I_D=19A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	4583	-	pF	$V_{GS}=0V, V_{DS}=15V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	492	-		
Reverse Transfer Capacitance	C_{rss}	-	459	-		
Gate Total Charge	Q_G	-	100	-	nC	$V_{GS}=10V, V_{DS}=15V,$ $I_D=19A$
Gate-Source charge	Q_{gs}	-	17	-		
Gate-Drain charge	Q_{gd}	-	18	-		
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	$V_{GS}=10V, V_{DD}=15V,$ $R_{G_ext}=3.0\Omega, I_D=19A$
Rise time	t_r	-	40	-		
Turn-off delay time	$t_{d(off)}$	-	76	-		
Fall time	t_f	-	24	-		
Gate resistance	R_G	-	1.6	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.77	1.4	V	$V_{GS}=0V, I_{SD}=19A$
Body Diode Reverse Recovery Time	t_{rr}		20		ns	$I_F=19A,$ $dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}		6		nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

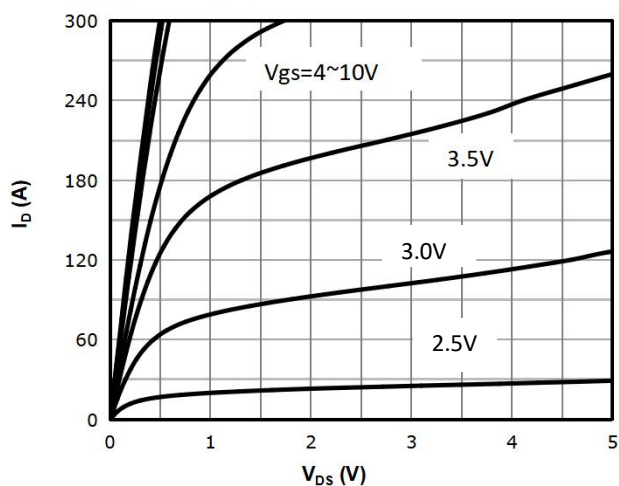


Fig 2: Transfer Characteristics

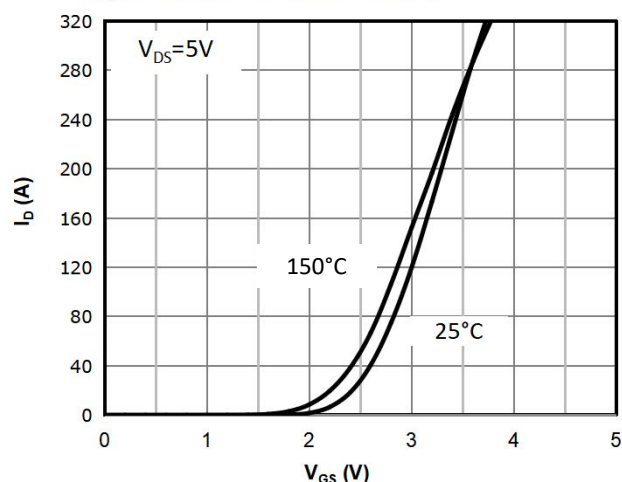


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

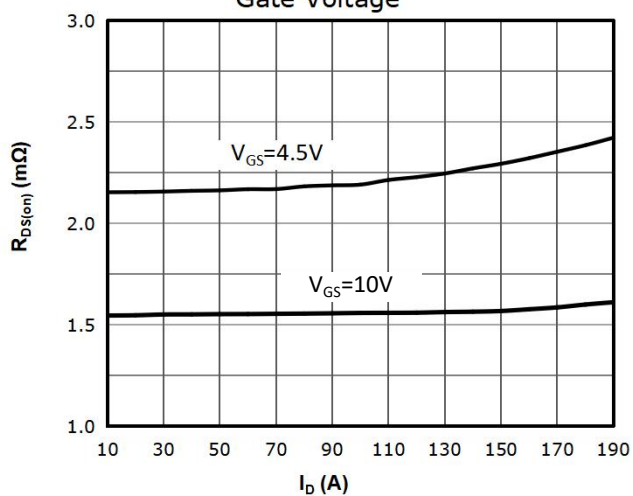


Fig 4: $R_{DS(on)}$ vs Gate Voltage

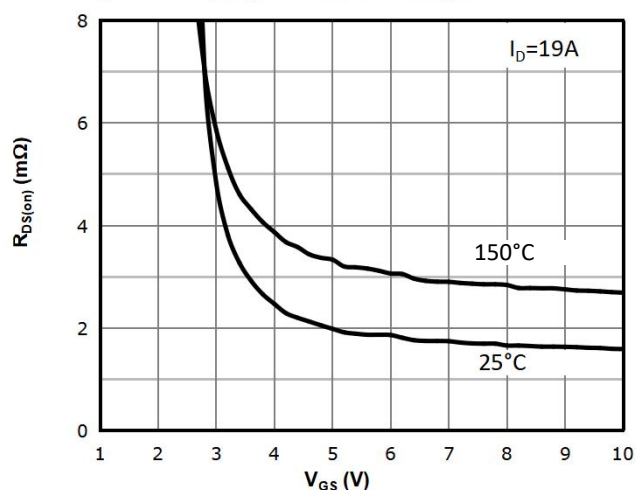


Fig 5: $R_{DS(on)}$ vs. Temperature

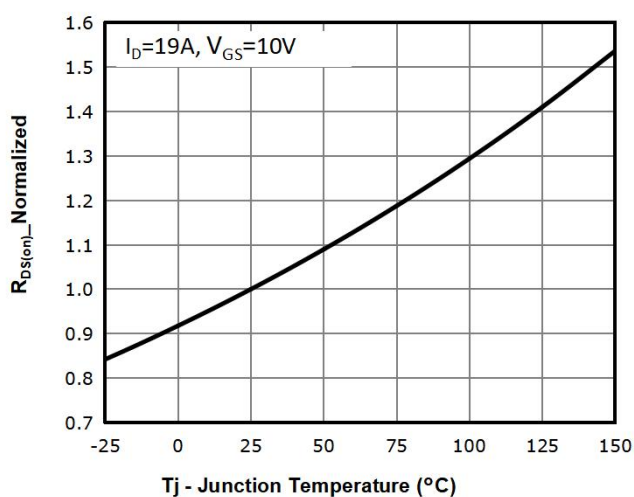


Fig 6: $V_{GS(th)}$ vs. Temperature

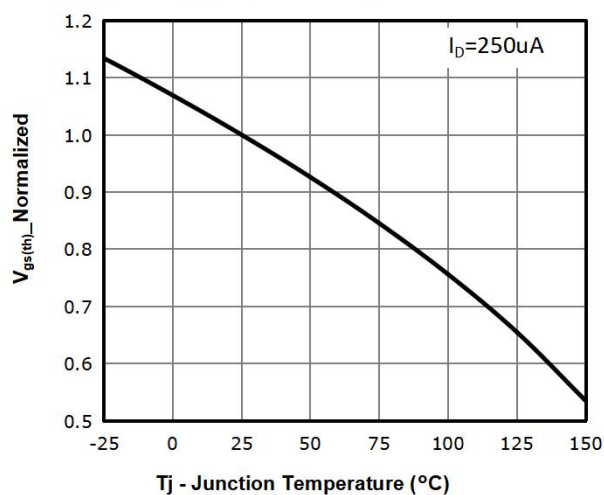


Fig 7: BVdss vs. Temperature

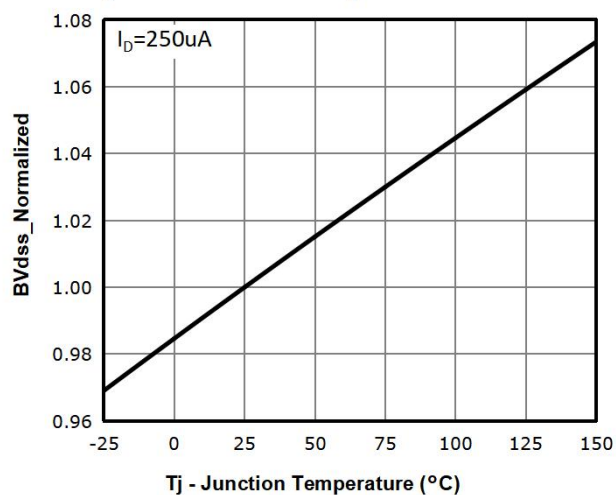


Fig 8: Capacitance Characteristics

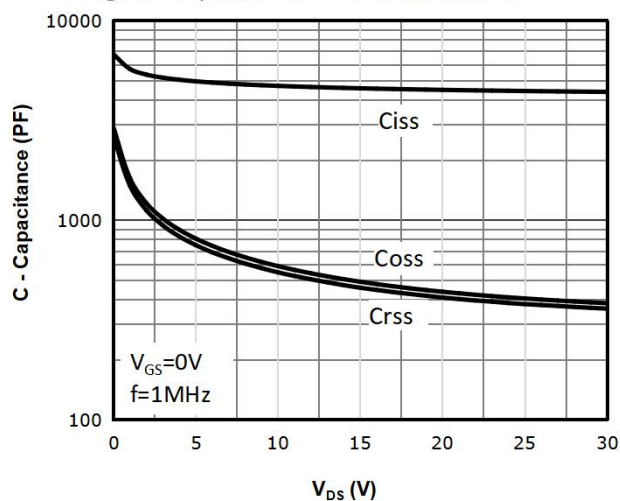


Fig 9: Gate Charge Characteristics

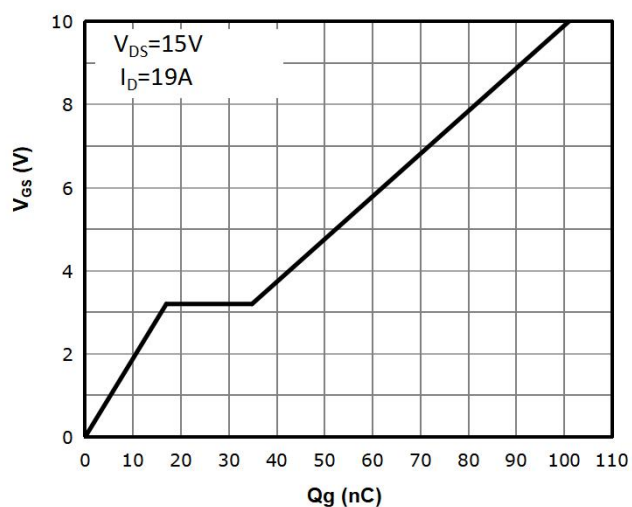


Fig 10: Body-diode Forward Characteristics

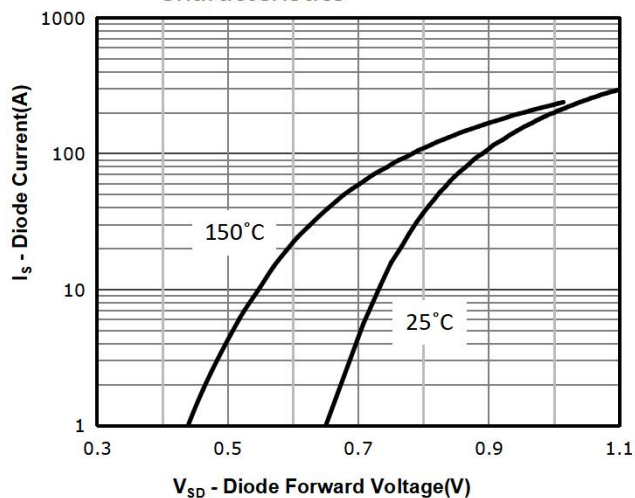


Fig 11: Power Dissipation

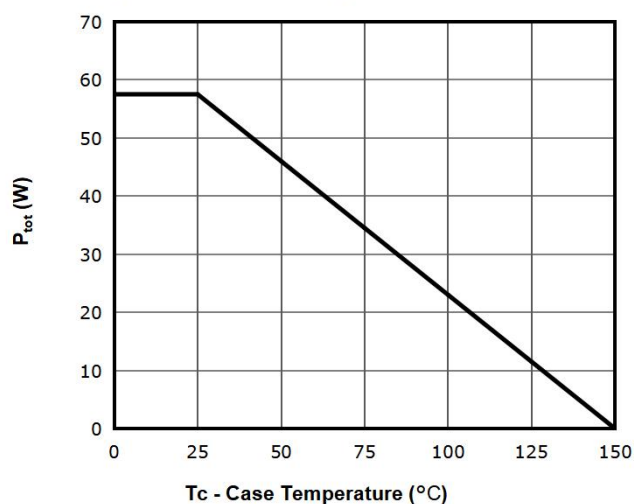


Fig 12: Drain Current Derating

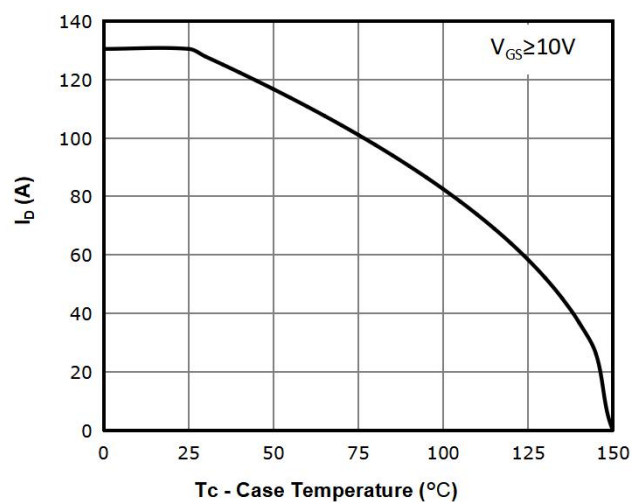


Fig 13: Safe Operating Area

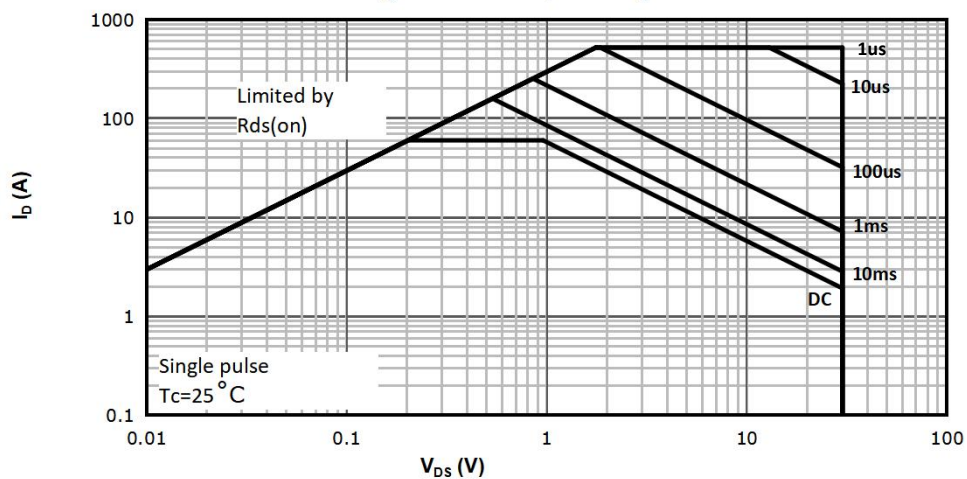
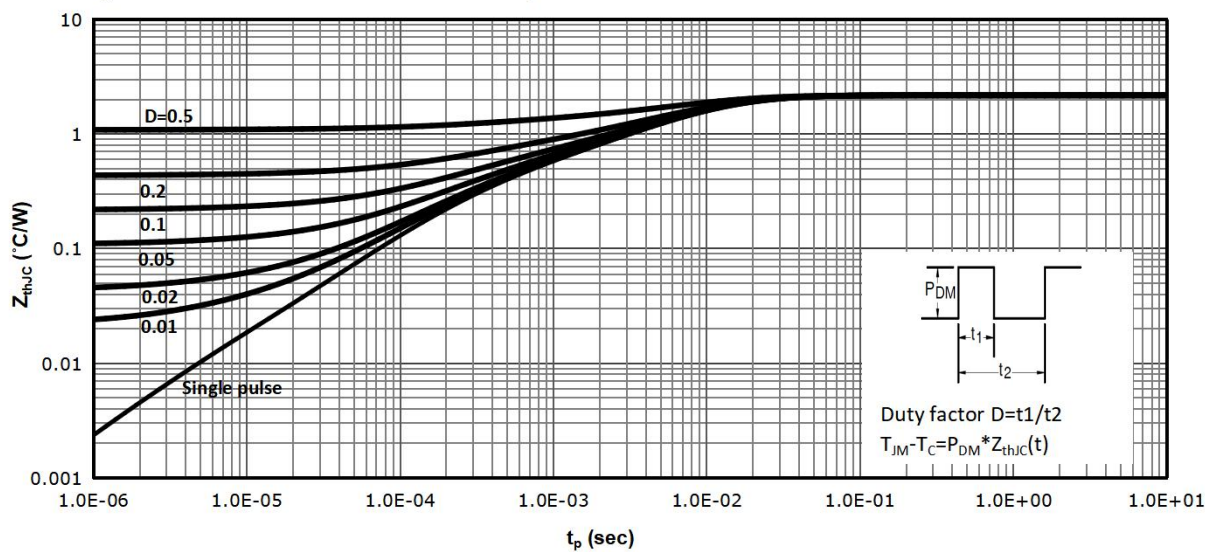
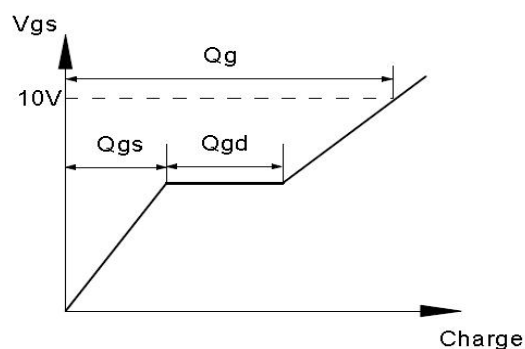
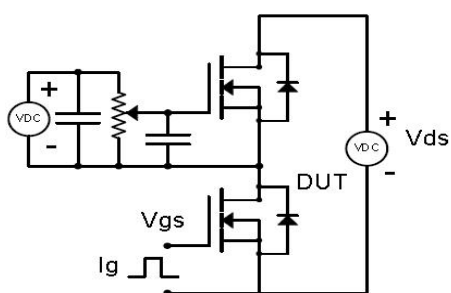


Fig 14: Max. Transient Thermal Impedance

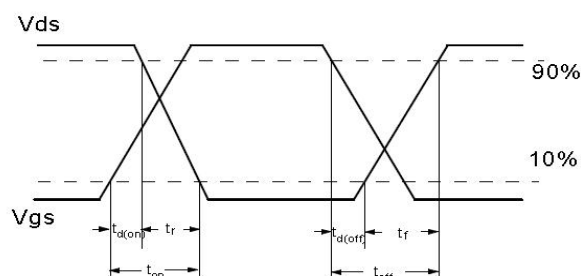
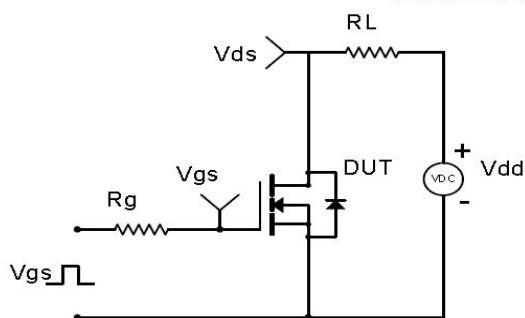


Test Circuit & Waveform

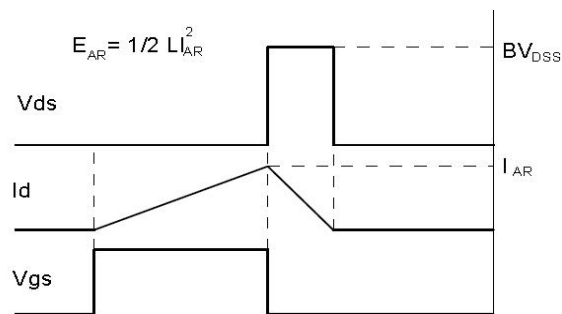
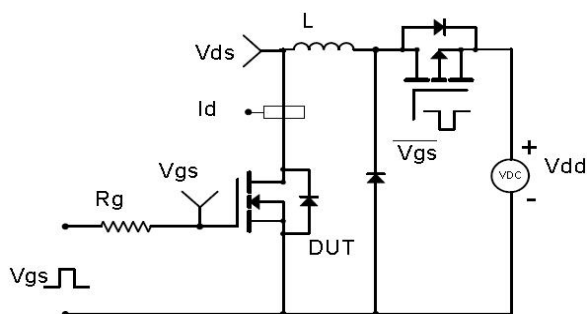
Gate Charge Test Circuit & Waveform



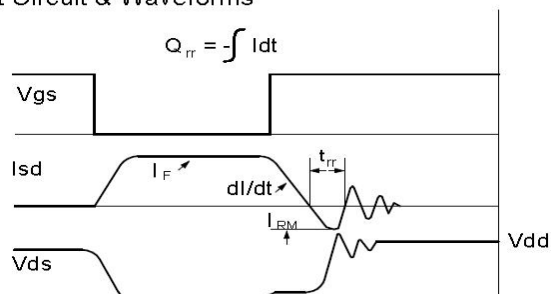
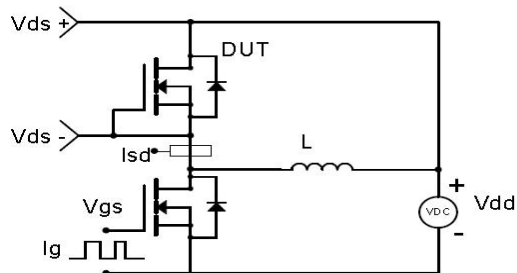
Resistive Switching Test Circuit & Waveforms

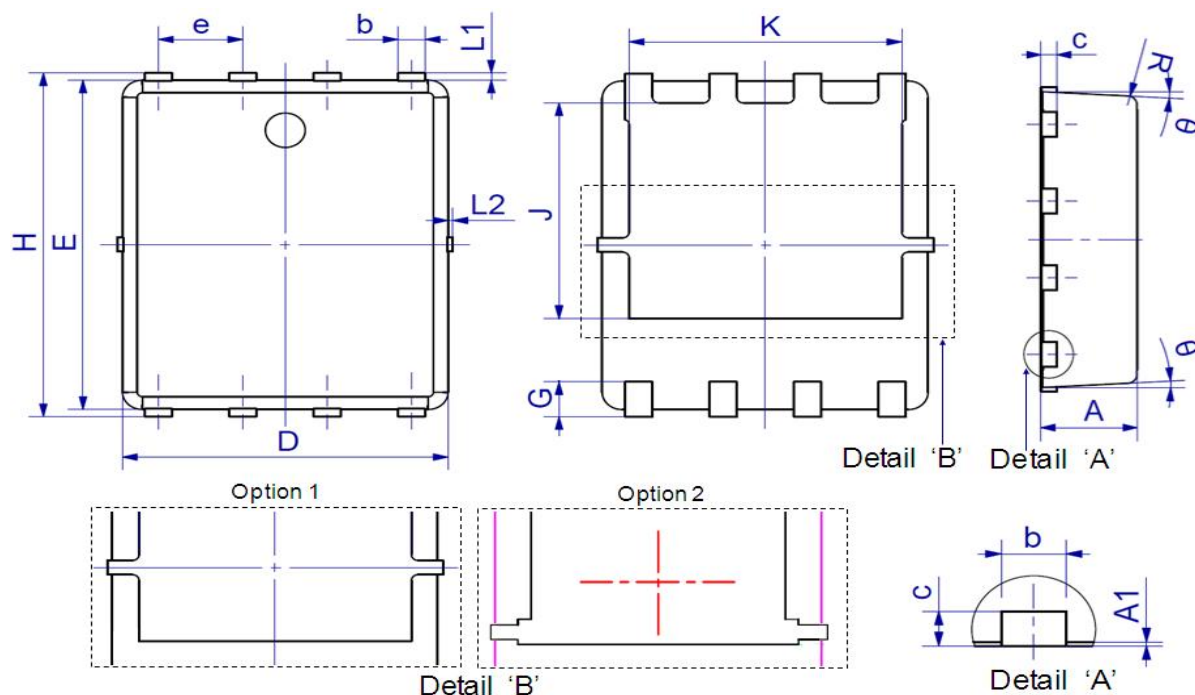


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: PDFN5X6


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D	4.80	5.40	0.189	0.213
e	1.27 BSC		0.050 BSC	
E	5.66	6.06	0.223	0.239
G	0.30	0.71	0.012	0.028
H	5.90	6.35	0.232	0.250
J	3.32	3.92	0.131	0.154
K	3.61	4.25	0.142	0.167
L1	0.05	0.25	0.002	0.010
L2	0.00	0.15	0.000	0.006
R	0.25 REF		0.010 REF	
θ	0°	12°	0°	12°

Marking



NOTE:

NXBBAAAA-Y

N	—Wire Bond code
X	—Assembly location code
BB	—Fab code
AAAA	—Lot code
Y	—Bin code



Revision History

Revision	Date	Major changes
1.0	2025/7/8	Release of Preliminary version.

Disclaimer

CRM reserves the right to change any product or information in this Specification at any time without prior notice.

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